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High-Power LEDs Lighting Systems Reliability - Understanding of Degradation Processes

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Abstract
With the progress of LED lighting technologies, their application is spreading in sign and display devices, spot lighting, base lighting, and security lighting, and new applications that cannot be realized with conventional light sources are expected. The reliability of LED is key to its application system.

Keywords: degradation mechanisms, failure modes, packaging, phosphors, ESD, EOS, thermal management

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